

AMENDMENT TO THE CLAIMS

1.-3. (Canceled)

4. (Currently Amended) ~~The method of claim 3 further~~ A method comprising:
selecting a dicing tape with an adhesive layer that has a thickness greater than a height of
one or more bump electrodes formed on a first side of a wafer, wherein the wafer is a double
bumped wafer with bump electrodes formed on a second side ;
applying the dicing tape to the first side of the wafer using a mounting pressure roller
such that the adhesive layer contacts and conforms to the one or more bump electrodes;
dicing the wafer from the second side of the wafer opposite the first side, the dicing
extending into the adhesive layer a distance less than a thickness of the adhesive layer; and
after dicing, reducing an adhesive strength of the adhesive layer by exposing the adhesive
layer to radiation.

5. (Original) The method of claim 4 wherein the bump electrodes have a height of
approximately 60 microns and the adhesive layer has a thickness of approximately 130 microns.

6. (Previously Presented) The method of claim 5, wherein dicing comprises:
dicing the wafer using a dual-blade dicing process wherein a first blade dices through less
than an entire thickness of the wafer followed by a second blade that dices through the wafer.

7. (Canceled)

8. (Previously Presented) The method of claim 4 wherein the adhesive strength is reduced
from a pre-radiation adhesive strength of approximately 200 grams/25 mm² to a post-radiation
adhesive strength of approximately 2 grams/25 mm².

9.-17. (Canceled)

18. (Currently Amended) The method of ~~claim 14~~claim 19 wherein the dicing tape is applied using a mounting pressure roller wherein the adhesive layer helps to distribute a pressure applied by the mounting pressure roller.

19. (Currently Amended) ~~The method of claim 14~~A method comprising:
determining a height of one or more bump electrodes on a first side of a wafer surface;
selecting a dicing tape based upon the determined height of the one or more bump electrodes, a first side of the dicing tape comprising an adhesive layer thicker than the determined height of the one or more bump electrodes;
applying the first side of the dicing tape to the first side of the wafer such that the adhesive layer contacts and conforms to the one or more bump electrodes; and
dicing the wafer from a second side of the wafer opposite the first side, the dicing extending into the adhesive layer a distance less than a thickness of the adhesive layer,
wherein the dicing tape is a radiation sensitive tape having a pre-radiation adhesive strength of approximately 200 grams/25 mm², and a post-radiation adhesive strength of approximately 2 grams/25 mm².

20. (Currently Amended) The method of ~~claim 14~~claim 19 wherein the bump electrodes have a height of approximately 60 microns and the adhesive layer has a thickness of approximately 130 microns.

21. (Previously Presented) The method of claim 20 further comprising:
dicing the wafer using a dual-blade dicing process.

22. (Previously Presented) The method of claim 21 further comprising:
wherein reducing an adhesive strength comprises irradiating a second side of the dicing tape.

23.-27. (Canceled)